

AMENDMENTS TO THE CLAIMS

1. (Currently amended) A semiconductor laser device in which a plurality of semiconductor lasers are juxtaposed on a semiconductor substrate,
the semiconductor lasers each comprising:
an active layer;
a first cladding layer and a second cladding layer arranged on both sides of the active layer;
and
a contact layer located on the second cladding layer, wherein
part of the second cladding layer and the contact layer constitutes a ridge portion, and
the semiconductor laser device comprising:
a light confinement layer, which is provided in a region other than an upper surface of the ridge portion of each of the second cladding layers and has a refractive index different from that of the second cladding layers; and
a dielectric film provided on the light confinement layer, wherein
the light confinement layer is sufficiently thin such that it does not function as a current constriction layer, wherein side surfaces of the part of the second cladding layer and the contact layer constituting the ridge portion are covered with the light confinement layer and the dielectric film.

2. (Original) The semiconductor laser device as claimed in claim 1, wherein
the dielectric film functions as a current constriction layer that flows no current in portions other than the ridge portion.

3. (Original) The semiconductor laser device as claimed in claim 2, wherein
the dielectric film is an insulation film.

4. (Original) The semiconductor laser device as claimed in claim 1, wherein
the dielectric film has a film thickness of not greater than 0.5 μm .

5. (Original) The semiconductor laser device as claimed in claim 1, wherein the light confinement layer has a conductive type opposite to that of the second cladding layer.

6. (Canceled)

7. (Original) The semiconductor laser device as claimed in claim 1, wherein the light confinement layer functions as a loss guide that absorbs light from the active layer and confines light in the second cladding layer.

8. (Original) The semiconductor laser device as claimed in claim 1, wherein the light confinement layer has a film thickness of not greater than 2 μm .

9. (Original) A method for manufacturing the semiconductor laser device claimed in claim 1, comprising the step of:

growing the dielectric layer on side surfaces of the ridge portion and on back surfaces of sidewise protrusions of the ridge portion by a chemical vapor deposition method.